TLV6710 Micropower, 36-V Window Comparator With 400-mV Reference

1 Features

- High Supply Voltage Range: 1.8 V to 36 V
- Adjustable Threshold: Down to 400 mV
- High Threshold Accuracy:
  - 0.25% (Typical)
  - 0.75% Max Over Temperature
- Low Quiescent Current: 7 µA (Typical)
- Open-Drain Outputs
- Internal Hysteresis: 5.5 mV (Typical)
- Temperature Range: –40°C to 125°C
- Package: Thin SOT-23-6

2 Applications

- Notebook PCs and Tablets
- Smartphones
- Digital Cameras
- Video Game Controllers
- Relays and Circuit Breakers
- Portable Medical Devices
- Door and Window Sensors
- Portable- and Battery-Powered Products

3 Description

The TLV6710 is a high voltage window comparator that operates over a 1.8 V to 36 V range. The device has two high-accuracy comparators with an internal 400-mV reference and two open-drain outputs rated to 25 V. The TLV6710 can be used as a window comparator or as two independent comparators; the monitored voltage can be set with the use of external resistors.

OUTA is driven low when the voltage at INA+ drops below (V_{ITP} – V_{HYS}), and goes high when the voltage returns above the respective threshold (V_{ITP}). OUTB is driven low when the voltage at INB– rises above V_{ITP}, and goes high when the voltage drops below the respective threshold (V_{ITP} – V_{HYS}). Both comparators in the TLV6710 include built-in hysteresis to reject brief glitches, thereby ensuring stable output operation without false triggering.

The TLV6710 is available in a Thin SOT-23-6 package and is specified over the junction temperature range of –40°C to 125°C.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TLV6710	SOT-23 (6)	2.90 mm × 1.60 mm

(1) For all available packages, see the package option addendum at the end of the data sheet.

Simplified Block Diagram

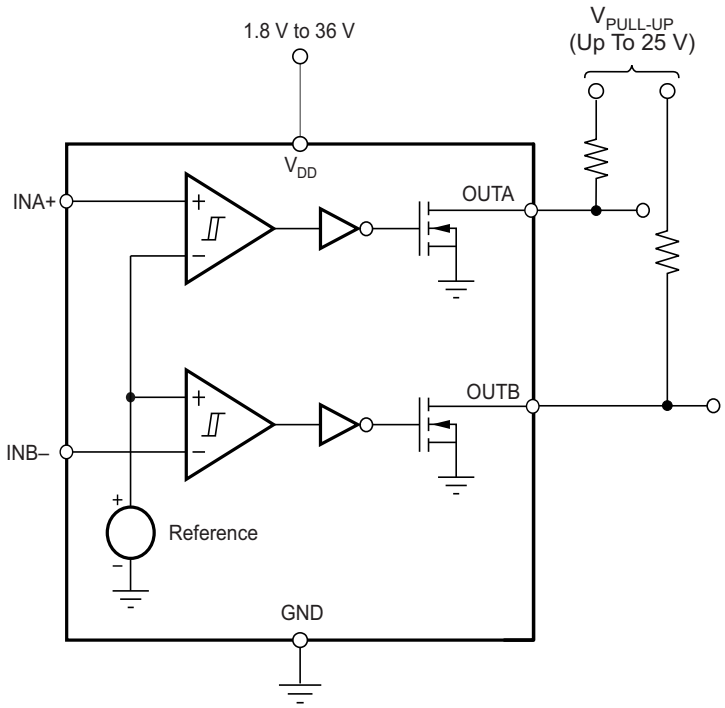


Table of Contents

4 Revision History

Changes from Revision A (April 2018) to Revision B — **Page**

- Changed output Description text from 36V to 25V on front page Simplified Block Diagram, Description and Application Information sections. ... 1

Changes from Original (January 2018) to Revision A — **Page**

- Changed Advance Information to Production Data ... 1

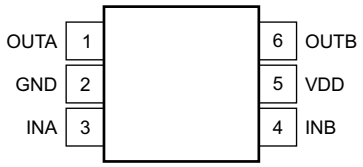
5 Device Comparison Table

Table 1. TLV67xx Integrated Comparator Family

PART NUMBER	CONFIGURATION	OPERATING VOLTAGE RANGE	THRESHOLD ACCURACY OVER TEMPERATURE
TLV6700	Window	1.8V to 18V	1%
TLV6703	Non-Inverting Single Channel	1.8V to 18V	1%
TLV6710	Window	1.8V to 36V	0.75%
TLV6713	Non-Inverting Single Channel	1.8V to 36V	0.75%

6 Pin Configuration and Functions

DDC Package
SOT-6
(Top View)



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
GND	2	—	Ground
INA	3	I	Comparator A input. This pin is connected to the voltage to be monitored with the use of an external resistor divider. When the voltage at this terminal drops below the threshold voltage $V_{IT–(INA)}$, OUTA is driven low.
INB	4	I	Comparator B input. This pin is connected to the voltage to be monitored with the use of an external resistor divider. When the voltage at this terminal exceeds the threshold voltage $V_{IT+(INB)}$, OUTB is driven low.
OUTA	1	O	INA comparator open-drain output. OUTA is driven low when the voltage at this comparator is less than $V_{IT–(INA)}$. The output goes high when the sense voltage rises above $V_{IT+(INA)}$.
OUTB	6	O	INB comparator open-drain output. OUTB is driven low when the voltage at this comparator exceeds $V_{IT+(INB)}$. The output goes high when the sense voltage falls below $V_{IT–(INB)}$.
VDD	5	I	Supply voltage input. Connect a 1.8-V to 36-V supply to VDD to power the device. It is good analog design practice to place a 0.1-µF ceramic capacitor close to this pin.

7 Specifications

7.1 Absolute Maximum Ratings

Over operating junction temperature range, unless otherwise noted.(1)

		MIN	MAX	UNIT
Voltage(2)	V_{DD}	–0.3	+40	V
	V_{OUTA}, V_{OUTB}	–0.3	+28	V
	V_{INA}, V_{INB}	–0.3	+7	V
Current	Output pin current		40	mA
Temperature	Operating junction, T_J	–40	+125	°C
	Storage temperature, T_{stg}	–65	+150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to network ground terminal.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating junction temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{DD}	Supply pin voltage	1.8		36	V
V_{INA}, V_{INB}	Input pin voltage	0		1.7	V
V_{OUTA}, V_{OUTB}	Output pin voltage	0		25	V
I_{OUTA}, I_{OUTB}	Output pin current	0		10	mA
T_J	Junction temperature	–40	+25	+125	°C

7.4 Thermal Information

THERMAL METRIC(1)		TLV6710 DDC (SOT) 6 PINS	UNITS
$R_{\theta JA}$	Junction-to-ambient thermal resistance	201.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	47.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	51.2	°C/W
ψ_{JT}	Junction-to-top characterization parameter	0.7	°C/W
ψ_{JB}	Junction-to-board characterization parameter	50.8	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report (SPRA953).

7.5 Electrical Characteristics

Over the operating temperature range of T_J = –40°C to +125°C, 1.8 V ≤ V_{DD} < 36 V, and pullup resistors $RP_{1,2}$ = 100 kΩ, unless otherwise noted. Typical values are at T_J = 25°C and V_{DD} = 12 V.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{DD}	Supply voltage range		1.8		36	V
$V_{(POR)}$	Power-on reset voltage(1)	V_{OL} ≤ 0.2 V			0.8	V
$V_{IT–(INA)}$	INA pin negative input threshold voltage	V_{DD} = 1.8 V to 36 V	397	400	403	mV
$V_{IT+(INA)}$	INA pin positive input threshold voltage	V_{DD} = 1.8 V to 36 V	400	405.5	413	mV
$V_{HYS(INA)}$	INA pin hysteresis voltage ($HYS = V_{IT+(INA)} – V_{IT–(INA)}$)		2	5.5	12	mV
$V_{IT–(INB)}$	INB pin negative input threshold voltage	V_{DD} = 1.8 V to 36 V	387	394.5	400	mV
$V_{IT+(INB)}$	INB pin positive input threshold voltage	V_{DD} = 1.8 V to 36 V	397	400	403	mV
$V_{HYS(INB)}$	INB pin hysteresis voltage ($HYS = V_{IT+(INB)} – V_{IT–(INB)}$)		2	5.2	12	mV
V_{OL}	Low-level output voltage	V_{DD} = 1.8 V, I_{OUT} = 3 mA		130	250	mV
		V_{DD} = 5 V, I_{OUT} = 5 mA		150	250	mV
I_{IN}	Input current (at INA, INB pins)	V_{DD} = 1.8 V and 36 V, V_{INA}, V_{INB} = 6.5 V	–25	+1	+25	nA
		V_{DD} = 1.8 V and 36 V, V_{INA}, V_{INB} = 0.1 V	–15	+1	+15	nA
$I_{D(leak)}$	Open-drain output leakage current	V_{DD} = 1.8 V and 36 V, V_{OUT} = 25 V		10	300	nA
I_{DD}	Supply current	V_{DD} = 1.8 V – 36 V		8	11	µA
UVLO	Undervoltage lockout(2)	V_{DD} falling	1.3	1.5	1.7	V

(1) The lowest supply voltage (V_{DD}) at which output is active; $t_{r(VDD)}$ > 15 µs/V. If less than $V_{(POR)}$, the output is undetermined.
(2) When V_{DD} falls below UVLO, OUTA is driven low and OUTB goes to high impedance. The outputs cannot be determined if less than $V_{(POR)}$.

7.6 Timing Requirements

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
$t_{pd(HL)}$	High-to-low propagation delay(1)	V_{DD} = 24 V, ±10-mV input overdrive, R_L = 100 kΩ, V_{OH} = 0.9 × V_{DD}, V_{OL} = 250 mV		9.9		µs
$t_{pd(LH)}$	Low-to-high propagation delay(1)	V_{DD} = 24 V, ±10-mV input overdrive, R_L = 100 kΩ, V_{OH} = 0.9 × V_{DD}, V_{OL} = 250 mV		28.1		µs
$t_{d(start)}$(2)	Startup delay	V_{DD} = 5 V		155		µs
t_r	Output rise time	V_{DD} = 12 V, 10-mV input overdrive, R_L = 100 kΩ, C_L = 10 pF, V_O = (0.1 to 0.9) × V_{DD}		2.7		µs
t_f	Output fall time	V_{DD} = 12 V, 10-mV input overdrive, R_L = 100 kΩ, C_L = 10 pF, V_O = (0.9 to 0.1) × V_{DD}		0.12		µs

(1) High-to-low and low-to-high refers to the transition at the input pins (INA and INB).
(2) During power on, V_{DD} must exceed 1.8 V for at least 150 µs (typ) before the output state reflects the input condition.

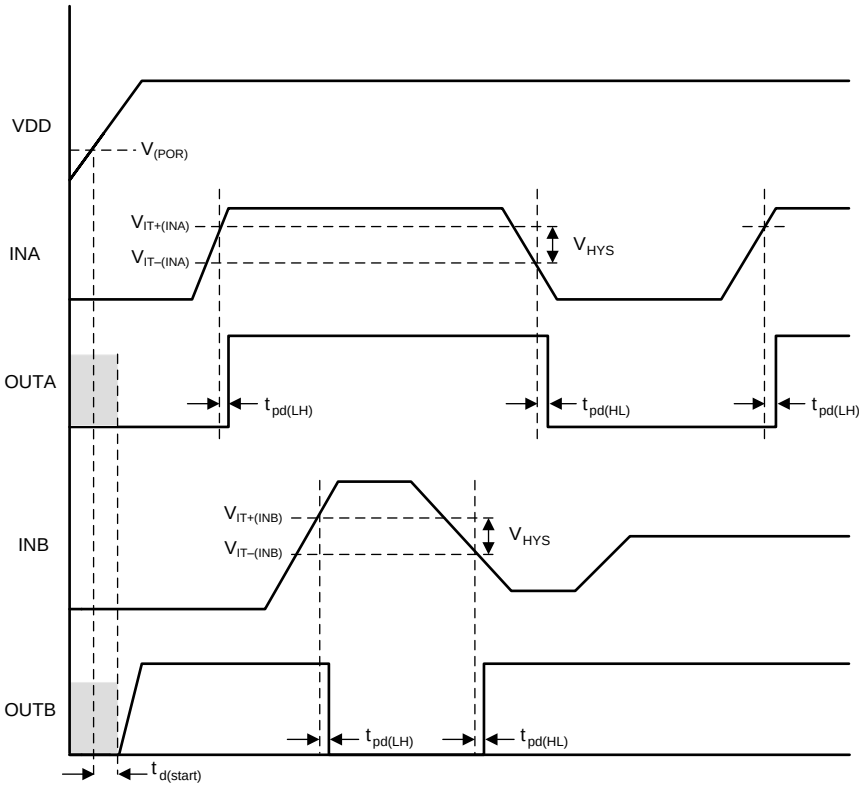


Figure 1. Timing Diagram

7.7 Typical Characteristics

At T_J = 25°C and V_{DD} = 12 V, unless otherwise noted.

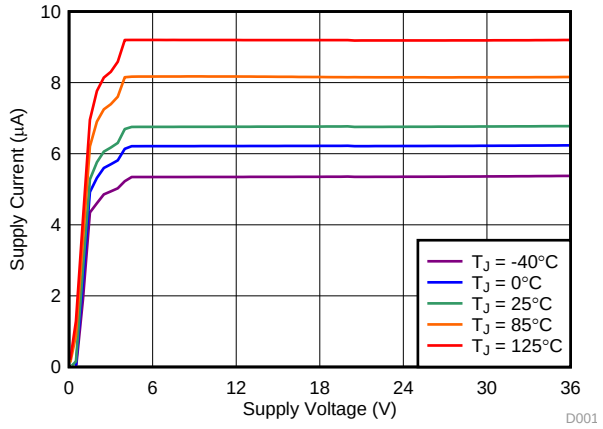
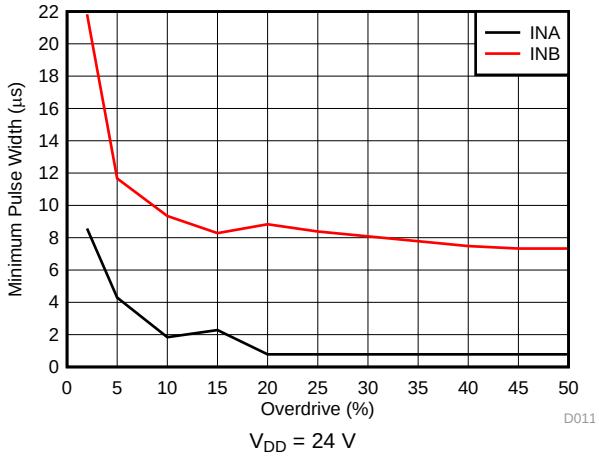


Figure 2. Supply Current vs Supply Voltage



V_{DD} = 24 V

Figure 3. Minimum Pulse Duration vs Threshold Overdrive Voltage(1) (1)

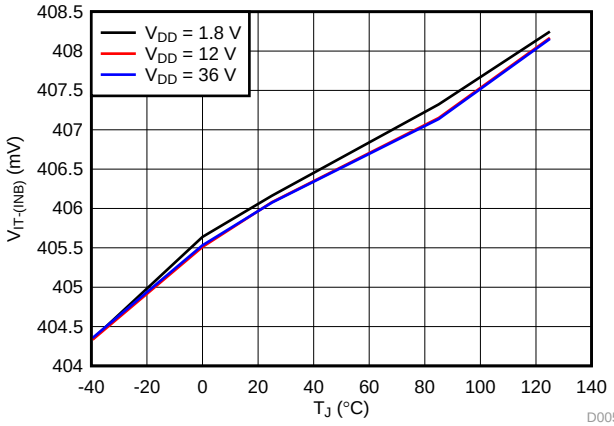


Figure 4. INA Positive Input Threshold Voltage ($V_{IT+(INA)}$) vs Temperature

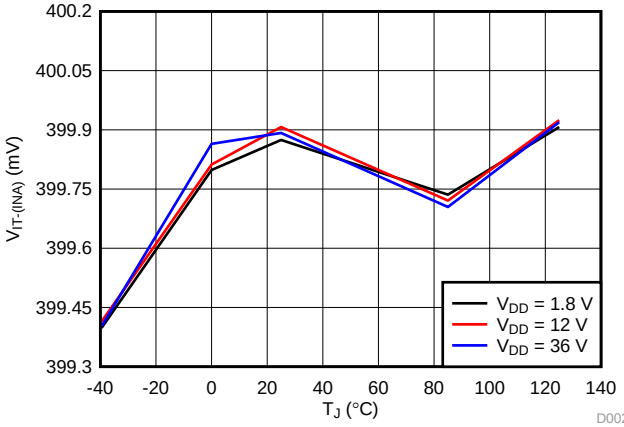


Figure 5. INA Negative Input Threshold Voltage ($V_{IT-(INA)}$) vs Temperature

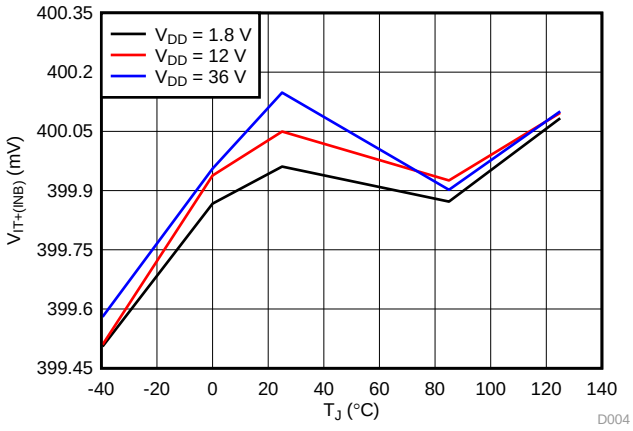


Figure 6. INB Positive Input Threshold Voltage ($V_{IT+(INB)}$) vs Temperature

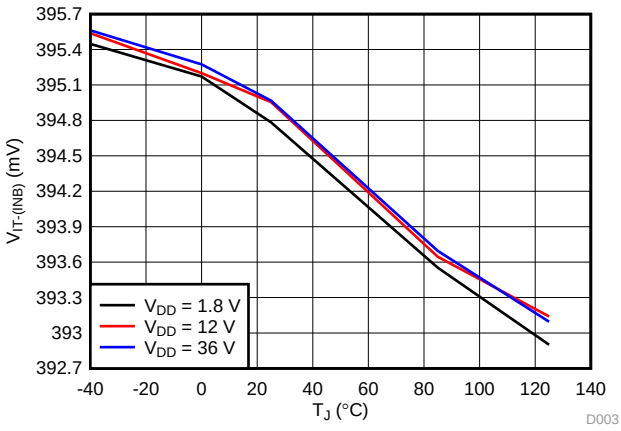


Figure 7. INB Negative Input Threshold Voltage ($V_{IT-(INB)}$) vs Temperature

(1) Minimum pulse duration required to trigger output high-to-low transition. INA = negative spike below V_{IT-} and INB = positive spike above V_{IT+}.

Typical Characteristics (continued)

At T_J = 25°C and V_{DD} = 12 V, unless otherwise noted.

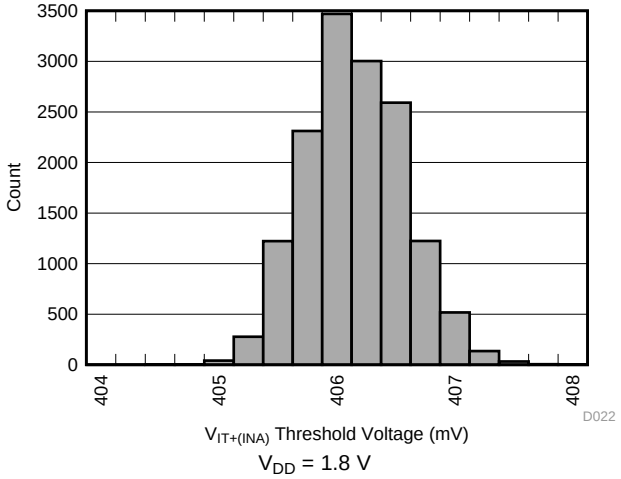


Figure 8. INA Positive Input Threshold Voltage ($V_{IT+(INA)}$) Distribution

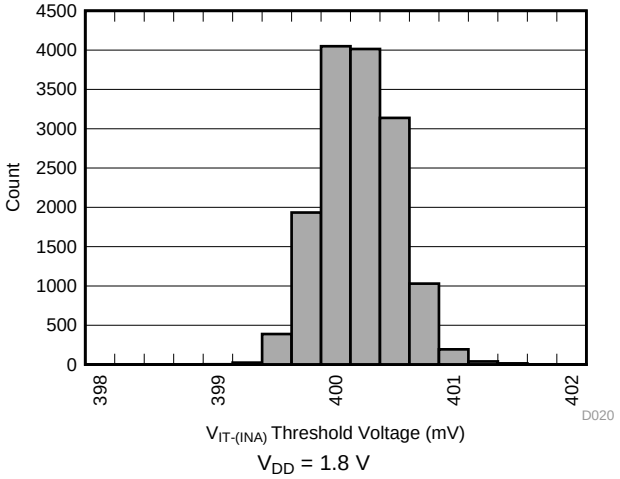


Figure 9. INA Negative Input Threshold Voltage ($V_{IT–(INA)}$) Distribution

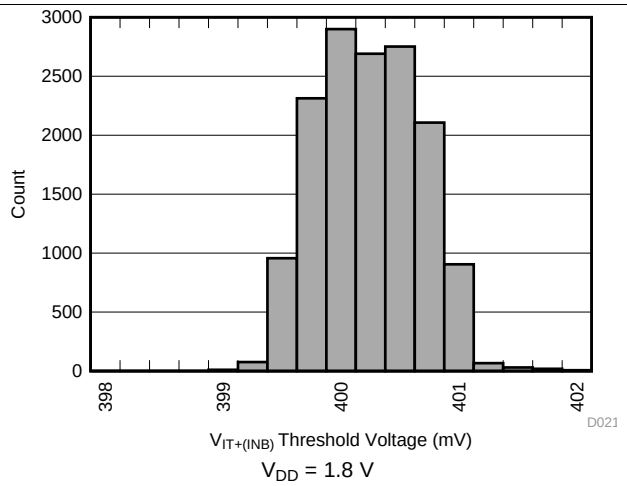


Figure 10. INB Positive Input Threshold Voltage ($V_{IT+(INB)}$) Distribution

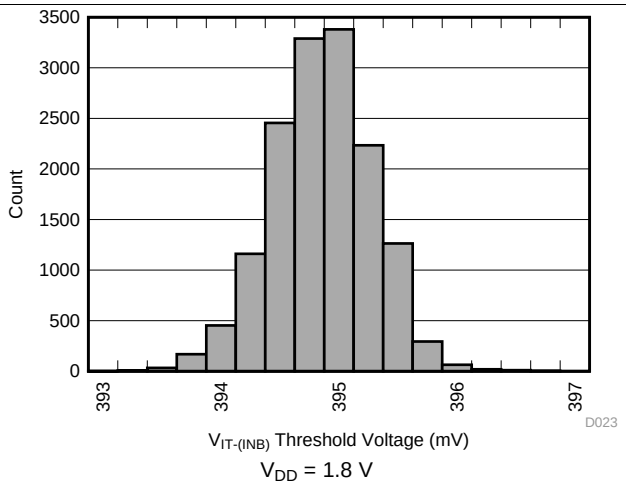


Figure 11. INB Negative Input Threshold Voltage ($V_{IT–(INB)}$) Distribution

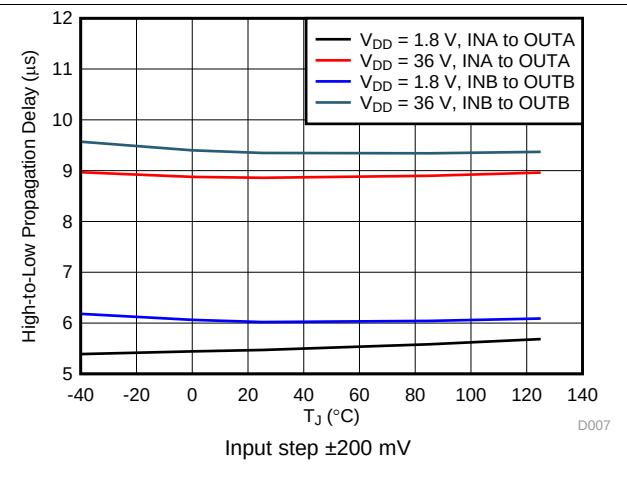


Figure 12. Propagation Delay vs Temperature (High-to-Low Transition at the Inputs)

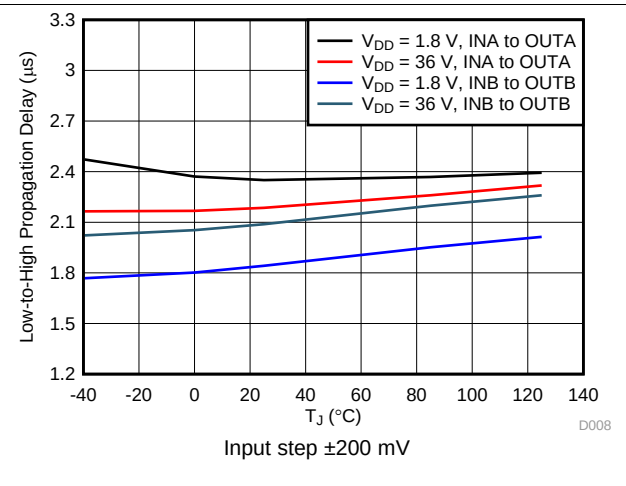


Figure 13. Propagation Delay vs Temperature (Low-to-High Transition at the Inputs)

Typical Characteristics (continued)

At T_J = 25°C and V_{DD} = 12 V, unless otherwise noted.

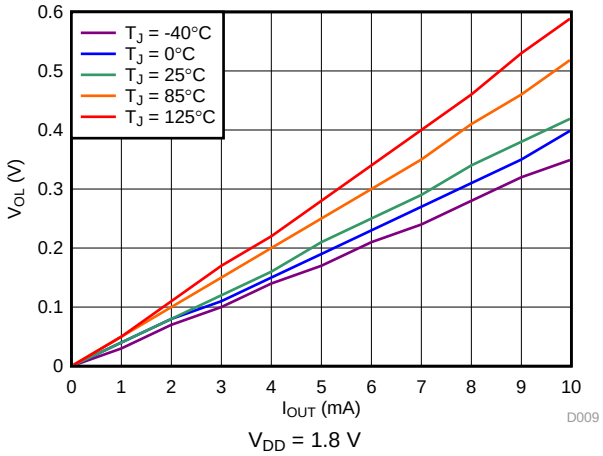


Figure 14. Output Voltage Low vs Output Sink Current

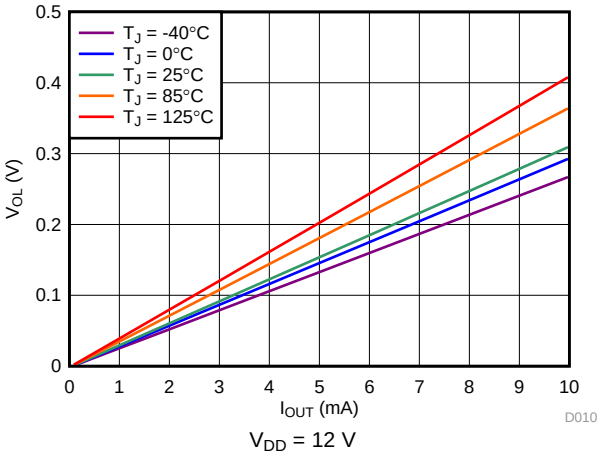


Figure 15. Output Voltage Low vs Output Sink Current

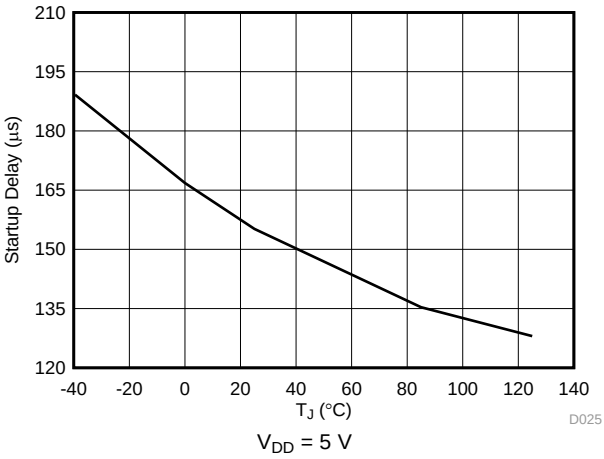


Figure 16. Start-Up Delay vs Temperature

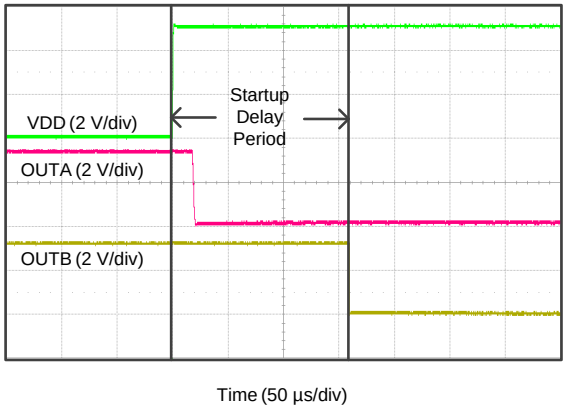


Figure 17. Start-Up Delay

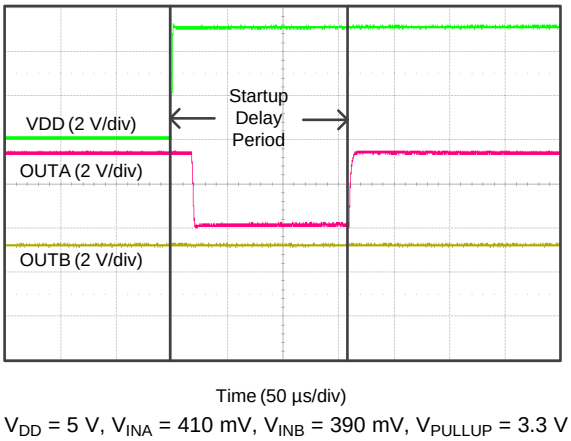


Figure 18. Start-Up Delay

8 Detailed Description

8.1 Overview

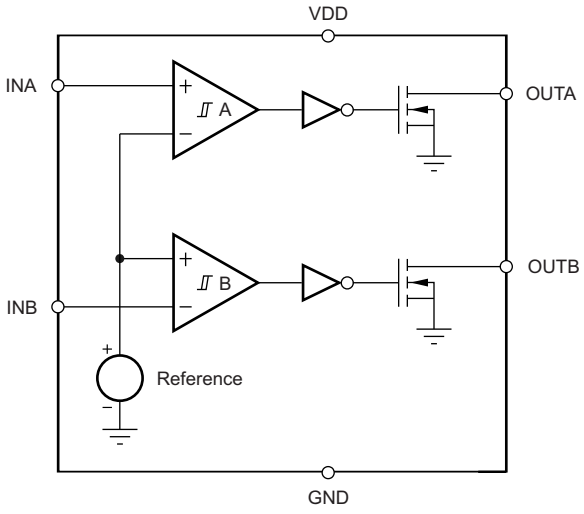
The TLV6710 combines two comparators (referred to as A and B) and a precision reference for overvoltage and undervoltage detection. The TLV6710 features a wide supply voltage range (1.8 V to 36 V) and high-accuracy window threshold voltages of 400 mV (0.75% over temperature) with built-in hysteresis. The outputs are rated to 25 V and can sink up to 10 mA.

Set each input pin (INA, INB) to monitor any voltage above 0.4 V by using an external resistor divider network. Each input pin has very low input leakage current, allowing the use of large resistor dividers without sacrificing system accuracy. To form a window comparator, use the two input pins and three resistors (see the *Window Comparator Considerations* section). In this configuration, the TLV6710 is designed to assert the output signals when the monitored voltage is within the window band. Each input can also be used independently. The relationship between the inputs and the outputs is shown in Table 2. Broad voltage thresholds are supported that enable the device to be used in a wide array of applications.

Table 2. Truth Table

CONDITION	OUTPUT	OUTPUT STATE
INA > $V_{IT+(INA)}$	OUTA high	Output A high impedance
INA < $V_{IT–(INA)}$	OUTA low	Output A sinking
INB > $V_{IT+(INB)}$	OUTB low	Output B sinking
INB < $V_{IT–(INB)}$	OUTB high	Output B high impedance

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Inputs (INA, INB)

The TLV6710 combines two comparators with a precision reference voltage. Each comparator has one external input; the other input is connected to the internal reference. The rising threshold on INB and the falling threshold on INA are designed and trimmed to be equal to the reference voltage (400 mV). This configuration optimizes the device accuracy when used as a window comparator. Both comparators also have built-in hysteresis that proves immunity to noise and ensures stable operation.

The comparator inputs swings from ground to 1.7 V (7.0 V absolute maximum), regardless of the device supply voltage used. Although not required in most cases, it is good analog design practice to place a 1-nF to 10-nF bypass capacitor at the comparator input for noisy applications in order to reduce sensitivity to transient voltage changes on the monitored signal.

For comparator A, the corresponding output (OUTA) is driven to logic low when the input INA voltage drops below $V_{IT-(INA)}$. When the voltage exceeds $V_{IT+(INA)}$, OUTA goes to a high-impedance state; see Figure 1.

For comparator B, the corresponding output (OUTB) is driven to logic low when the voltage at input INB exceeds $V_{IT+(INB)}$. When the voltage drops below $V_{IT-(INB)}$ OUTB goes to a high-impedance state; see Figure 1. Together, these two comparators form a window-detection function as described in the *Window Comparator Considerations* section.

8.3.2 Outputs (OUTA, OUTB)

In a typical TLV6710 application, the outputs are connected to a GPIO input of the processor (such as a digital signal processor [DSP], central processing unit [CPU], field-programmable gate array [FPGA], or application-specific integrated circuit [ASIC]).

The TLV6710 provides two open-drain outputs (OUTA and OUTB); use pullup resistors to hold these lines high when the output goes to a high-impedance state. Connect pullup resistors to the proper voltage rails to enable the outputs to be connected to other devices at correct interface voltage levels. The TLV6710 outputs can be pulled up to 25 V, independent of the device supply voltage. To ensure proper voltage levels, give some consideration when choosing the pullup resistor values. The pullup resistor value is determined by V_{OL}, output capacitive loading, and output leakage current ($I_{D(leak)}$). These values are specified in the *Electrical Characteristics* table. Use wired-OR logic to merge OUTA and OUTB into one logic signal.

Table 2 and the *Inputs (INA, INB)* section describe how the outputs are asserted or high impedance. See Figure 1 for a timing diagram that describes the relationship between threshold voltages and the respective output.

8.4 Device Functional Modes

8.4.1 Normal Operation (V_{DD} > UVLO)

When the voltage on VDD is greater than 1.8 V for at least 155 µs, the OUTA and OUTB signals correspond to the voltage on INA and INB as listed in Table 2.

8.4.2 Undervoltage Lockout ($V_{(POR)} < V_{DD} <$ UVLO)

When the voltage on VDD is less than the device UVLO voltage, and greater than the power-on reset voltage, $V_{(POR)}$, the OUTA and OUTB signals are asserted and high impedance, respectively, regardless of the voltage on INA and INB.

8.4.3 Power On Reset ($V_{DD} < V_{(POR)}$)

When the voltage on VDD is lower than the required voltage to internally pull the asserted output to GND ($V_{(POR)}$), both outputs are in a high-impedance state.

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TLV6710 device is a wide-supply voltage window comparator that operates over a V_{DD} range of 1.8 V to 36 V. The device has two high-accuracy comparators with an internal 400-mV reference and two open-drain outputs rated to 25 V for overvoltage and undervoltage detection. The device can be used either as a window comparator or as two independent voltage monitors. The monitored voltages are set with the use of external resistors.

9.1.1 Window Comparator Considerations

The inverting and noninverting configuration of the comparators forms a window-comparator detection circuit using a resistor divider network, as shown in Figure 19 and Figure 20. The input pins can monitor any system voltage above 400 mV with the use of a resistor divider network. INA and INB monitor for undervoltage and overvoltage conditions, respectively.

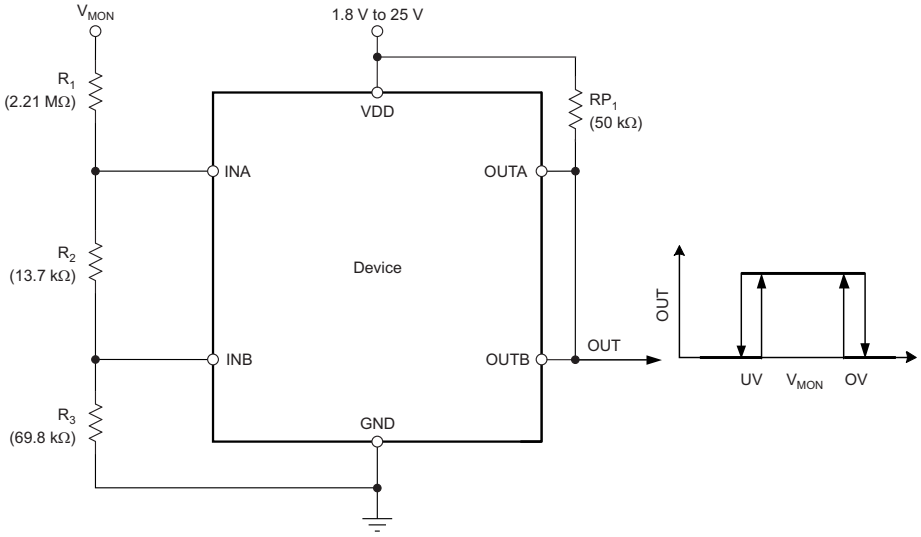


Figure 19. Window Comparator Block Diagram

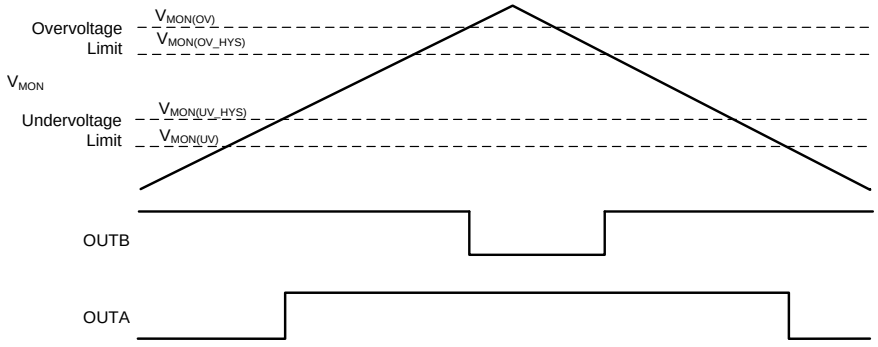


Figure 20. Window Comparator Timing Diagram

Application Information (continued)

The TLV6710 flags the overvoltage or undervoltage condition with the greatest accuracy. The highest accuracy threshold voltages are $V_{IT-(INA)}$ and $V_{IT+(INB)}$, and correspond with the falling undervoltage flag, and the rising overvoltage flag, respectively. These thresholds represent the accuracy when the monitored voltage is within the valid window (both OUTA and OUTB are in a high-impedance state), and correspond to the $V_{MON(UV)}$ and $V_{MON(OV)}$ trigger voltages, respectively. If the monitored voltage is outside of the valid window (V_{MON} is less than the undervoltage limit, $V_{MON(UV)}$, or greater than overvoltage limit, $V_{MON(OV)}$), then the input threshold voltages to re-enter the valid window are $V_{IT+(INA)}$ or $V_{IT-(INB)}$, and correspond with the $V_{MON(UV\_HYS)}$ and $V_{MON(OV\_HYS)}$ monitored voltages, respectively.

The resistor divider values and target threshold voltage can be calculated by using Equation 1 through Equation 4:

$$R_{TOTAL} = R_1 + R_2 + R_3 \quad (1)$$

Choose an R_{TOTAL} value so that the current through the divider is approximately 100 times higher than the input current at the INA and INB pins. Resistors with high values minimize current consumption; however, the input bias current degrades accuracy if the current through the resistors is too low. See application report *Optimizing Resistor Dividers at a Comparator Input* (SLVA450), for details on sizing input resistors.

R_3 is determined by Equation 2:

$$R_3 = \frac{R_{TOTAL}}{V_{MON(OV)}} \bullet V_{IT+(INB)} \quad (2)$$

where

- $V_{MON(OV)}$ is the target voltage at which an overvoltage condition is detected.

R_2 is determined by either Equation 3 or Equation 4:

$$R_2 = \left(\frac{R_{TOTAL}}{V_{MON(UV\_HYS)}} \bullet V_{IT+(INA)} \right) - R_3 \quad (3)$$

where

- $V_{MON(UV\_HYS)}$ is the target voltage at which an undervoltage condition is removed as V_{MON} rises.

$$R_2 = \left(\frac{R_{TOTAL}}{V_{MON(UV)}} \bullet V_{IT-(INA)} \right) - R_3 \quad (4)$$

where

- $V_{MON(UV)}$ is the target voltage at which an undervoltage condition is detected.

9.1.2 Input and Output Configurations

Figure 21 to Figure 23 show examples of the various input and output configurations.

Application Information (continued)

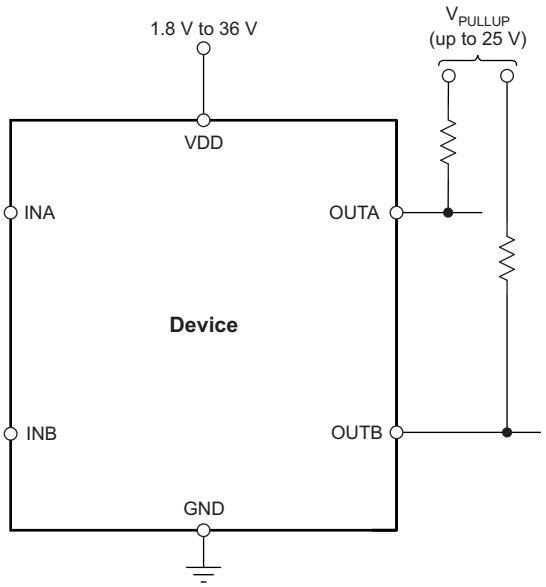


Figure 21. Interfacing to Voltages Other than V_{DD}

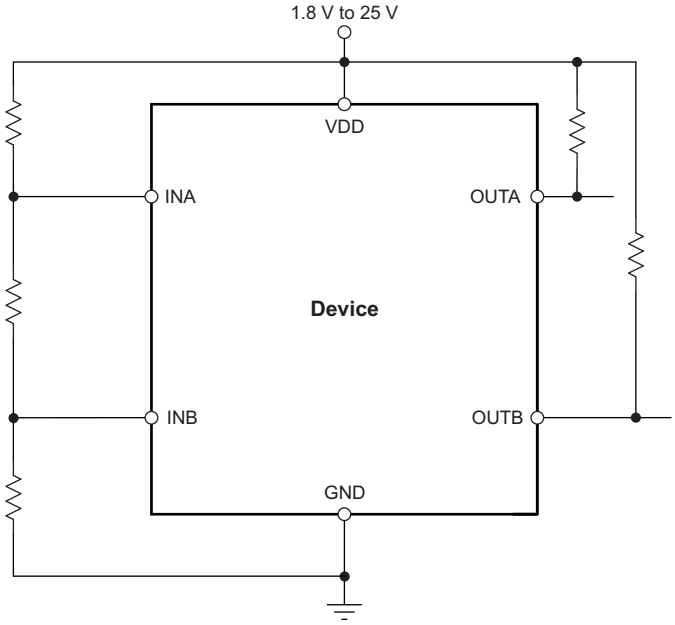
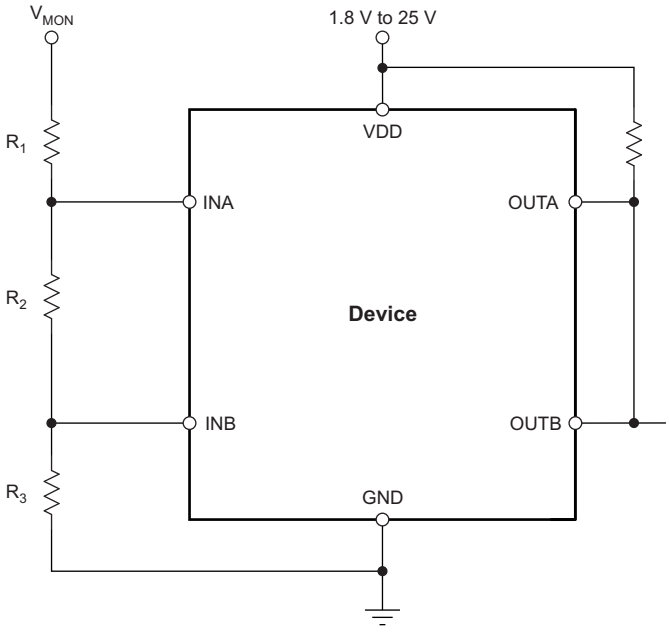


Figure 22. Monitoring the Same Voltage as V_{DD}

Application Information (continued)



NOTE: The inputs can monitor a voltage higher than V_{DD} (max) with the use of an external resistor divider network.

Figure 23. Monitoring a Voltage Other than V_{DD}

9.1.3 Immunity to Input Pin Voltage Transients

The TLV6710 is immune to short voltage transient spikes on the input pins. Sensitivity to transients depends on both transient duration and amplitude; see Figure 3, *Minimum Pulse Duration vs Threshold Overdrive Voltage*.

9.2 Typical Application

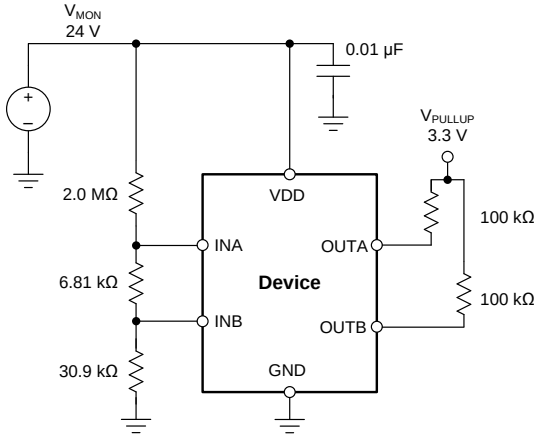


Figure 24. 24-V, 10% Window Comparator

Typical Application (continued)

9.2.1 Design Requirements

Table 3. Design Parameters

PARAMETER	DESIGN REQUIREMENT	DESIGN RESULT
Monitored voltage	24-V nominal, rising ($V_{MON(OV)}$) and falling ($V_{MON(UV)}$) threshold ±10% nominal (26.4 V and 21.6 V, respectively)	$V_{MON(OV)}$ = 26.4 V ±2.7%, $V_{MON(UV)}$ = 21.6 V ±2.7%
Output logic voltage	3.3-V CMOS	3.3-V CMOS
Maximum current consumption	30 µA	24 µA

9.2.2 Detailed Design Procedure

1. Determine the minimum total resistance of the resistor network necessary to achieve the current consumption specification by using Equation 1. For this example, the current flow through the resistor network was chosen to be 13 µA; a lower current can be selected, however, care should be taken to avoid leakage currents that are artifacts of the manufacturing process. Leakage currents significantly impact the accuracy if they are greater than 1% of the resistor network current.

$$R_{TOTAL} = \frac{V_{MON(OV)}}{I} = \frac{26.4\ V}{13\ \mu A} = 2.03\ M\Omega \quad (5)$$

   where
   - $V_{MON(OV)}$ is the target voltage at which an overvoltage condition is detected as V_{MON} rises.
   - I is the current flowing through the resistor network.

2. After R_{TOTAL} is determined, R_3 can be calculated using Equation 6. Select the nearest 1% resistor value for R_3. In this case, 30.9 kΩ is the closest value.

$$R_3 = \frac{R_{TOTAL}}{V_{MON(OV)}} \bullet V_{IT+(INB)} = \frac{2.03\ M\Omega}{26.4\ V} \bullet 0.4\ V = 30.7\ k\Omega \quad (6)$$

3. Use Equation 7 to calculate R2. Select the nearest 1% resistor value for R_2. In this case, 6.81 kΩ is the closest value.

$$R_2 = \frac{R_{TOTAL}}{V_{MON(UV)}} \bullet V_{IT-(INA+)} - R_3 = \frac{2.03\ M\Omega}{21.6\ V} \bullet 0.4\ V - 30.9\ k\Omega = 6.69\ k\Omega \quad (7)$$

4. Use Equation 8 to calculate R1. Select the nearest 1% resistor value for R_1. In this case, 2 MΩ is the closest value.

$$R_1 = R_{TOTAL} - R_2 - R_3 = 2.03\ M\Omega - 6.81\ k\Omega - 30.9\ k\Omega = 1.99\ M\Omega \quad (8)$$

5. The worst-case tolerance can be calculated by referring to Equation 13 in application report *Optimizing Resistor Dividers at a Comparator Input* (SLVA450). An example of the rising threshold error, $V_{MON(OV)}$, is given in Equation 9:

$$\%\ ACC = \%\ TOL(V_{IT+(INB)}) + 2 \bullet \left(1 - \frac{V_{IT+(INB)}}{V_{MON(OV)}}\right) \bullet \%\ TOL_R = 0.75\ \% + 2 \bullet \left(1 - \frac{0.4}{26.4}\right) \bullet 1\% = 2.72\ \% \quad (9)$$

   where
   - % TOL($V_{IT+(INB)}$) is the tolerance of the INB positive threshold.
   - % ACC is the total tolerance of the $V_{MON(OV)}$ voltage.
   - % TOL_R is the tolerance of the resistors selected.

6. When the outputs switch to the high-Z state, the rise time of the OUTA or OUTB node depends on the pullup resistance and the capacitance on the node. Choose pullup resistors that satisfy the downstream timing requirements; 100-kΩ resistors are a good choice for low-capacitive loads.

9.2.3 Application Curve

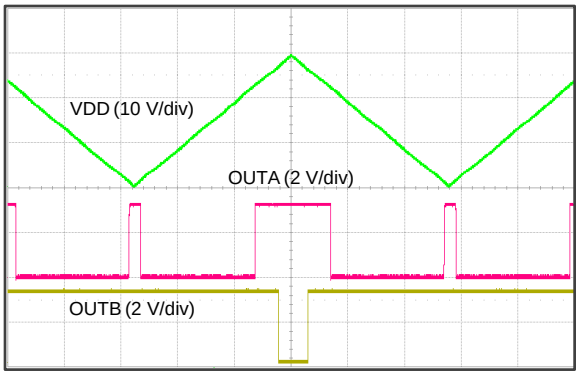


Figure 25. 24-V Window Monitor Output Response

9.3 Do's and Don'ts

It is good analog design practice to have a 0.1-µF decoupling capacitor from V_{DD} to GND.

If the monitored rail is noisy, connect decoupling capacitors from the comparator inputs to GND.

Do not use resistors for the voltage divider that cause the current through them to be less than 100 times the input current of the comparators without also accounting for the effect to the accuracy.

Do not use pullup resistors that are too small, because the larger current sunk by the output then exceeds the desired low-level output voltage (V_{OL}).

10 Power Supply Recommendations

The TLV6710 has a 40-V absolute maximum rating on the VDD pin, with a recommended operating condition of 36 V. If the voltage supply that is providing power to VDD is susceptible to any large voltage transient that may exceed 40 V, or if the supply exhibits high voltage slew rates greater than 1 V/µs, take additional precautions. Place an RC filter between the supply and VDD to filter any high-frequency transient surges on the VDD pin. A 100-Ω resistor and 0.01-µF capacitor is required in these cases, as shown in Figure 26.

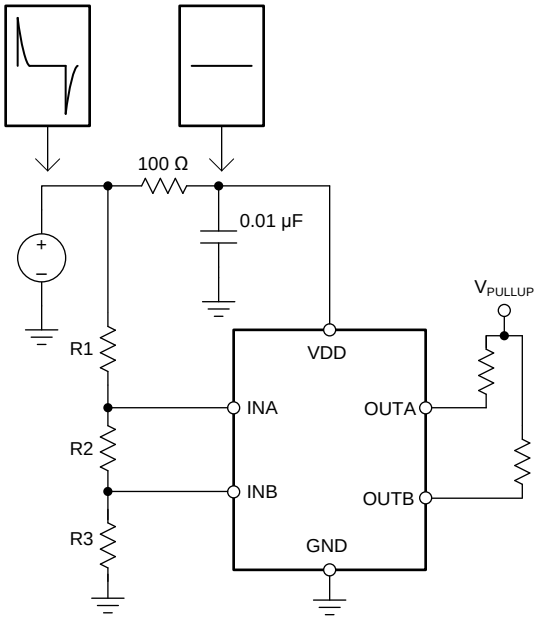


Figure 26. Using an RC Filter to Remove High-Frequency Disturbances on VDD

11 Layout

11.1 Layout Guidelines

- Place R_1, R_2, and R_3 close to the device to minimize noise coupling into the INA and INB nodes.
- Place the VDD decoupling capacitor close to the device.
- Avoid using long traces for the VDD supply node. The VDD capacitor (C_{VDD}), along with parasitic inductance from the supply to the capacitor, may form an LC tank and create ringing with peak voltages above the maximum VDD voltage. If this is unavoidable, see Figure 26 for an example of filtering VDD.

11.2 Layout Example

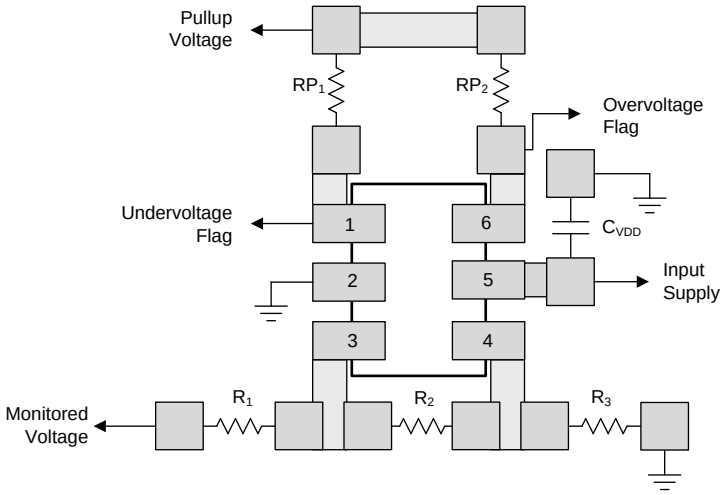


Figure 27. Recommended Layout

12 Device and Documentation Support

12.1 Device Support

12.1.1 Development Support

The *DIP Adapter Evaluation Module* allows conversion of the SOT-23-6 package to a standard DIP-6 pinout for ease of prototyping and bench evaluation.

12.2 Documentation Support

12.2.1 Related Documentation

For related documentation, see the following:

Optimizing Resistor Dividers at a Comparator Input (SLVA450)

12.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.4 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.5 Trademarks

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

12.6 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.7 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TLV6710DDCR	Active	Production	SOT-23-THIN (DDC) | 6	3000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1I61
TLV6710DDCR.A	Active	Production	SOT-23-THIN (DDC) | 6	3000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1I61
TLV6710DDCRG4	Active	Production	SOT-23-THIN (DDC) | 6	3000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1I61
TLV6710DDCRG4.A	Active	Production	SOT-23-THIN (DDC) | 6	3000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1I61
TLV6710DDCT	Active	Production	SOT-23-THIN (DDC) | 6	250 | SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1I61
TLV6710DDCT.A	Active	Production	SOT-23-THIN (DDC) | 6	250 | SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1I61

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

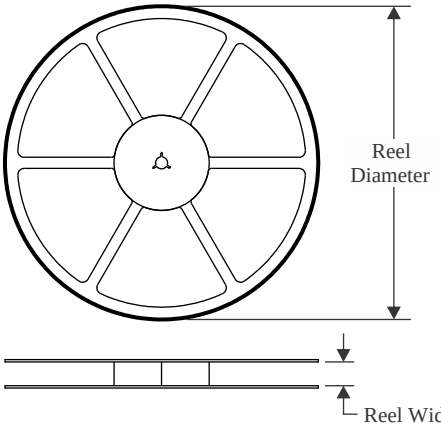
(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

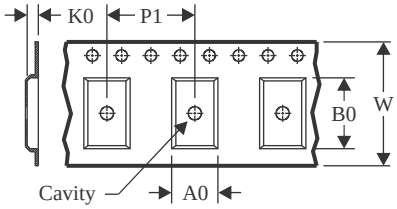
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

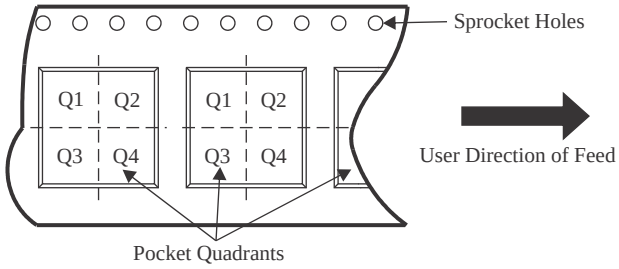


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

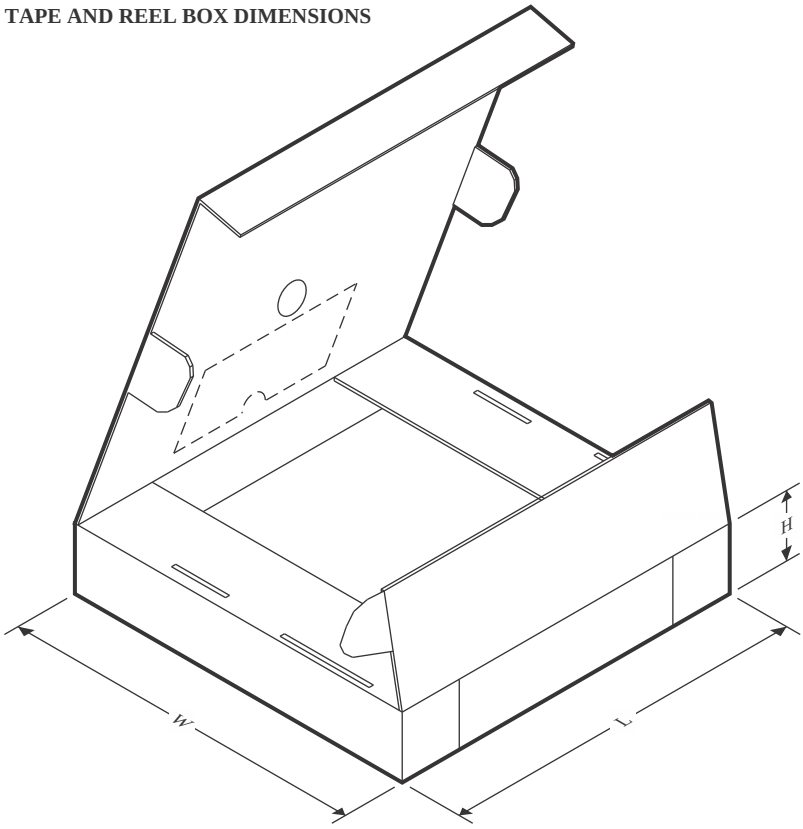
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV6710DDCR	SOT-23-THIN	DDC	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV6710DDCRG4	SOT-23-THIN	DDC	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV6710DDCT	SOT-23-THIN	DDC	6	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

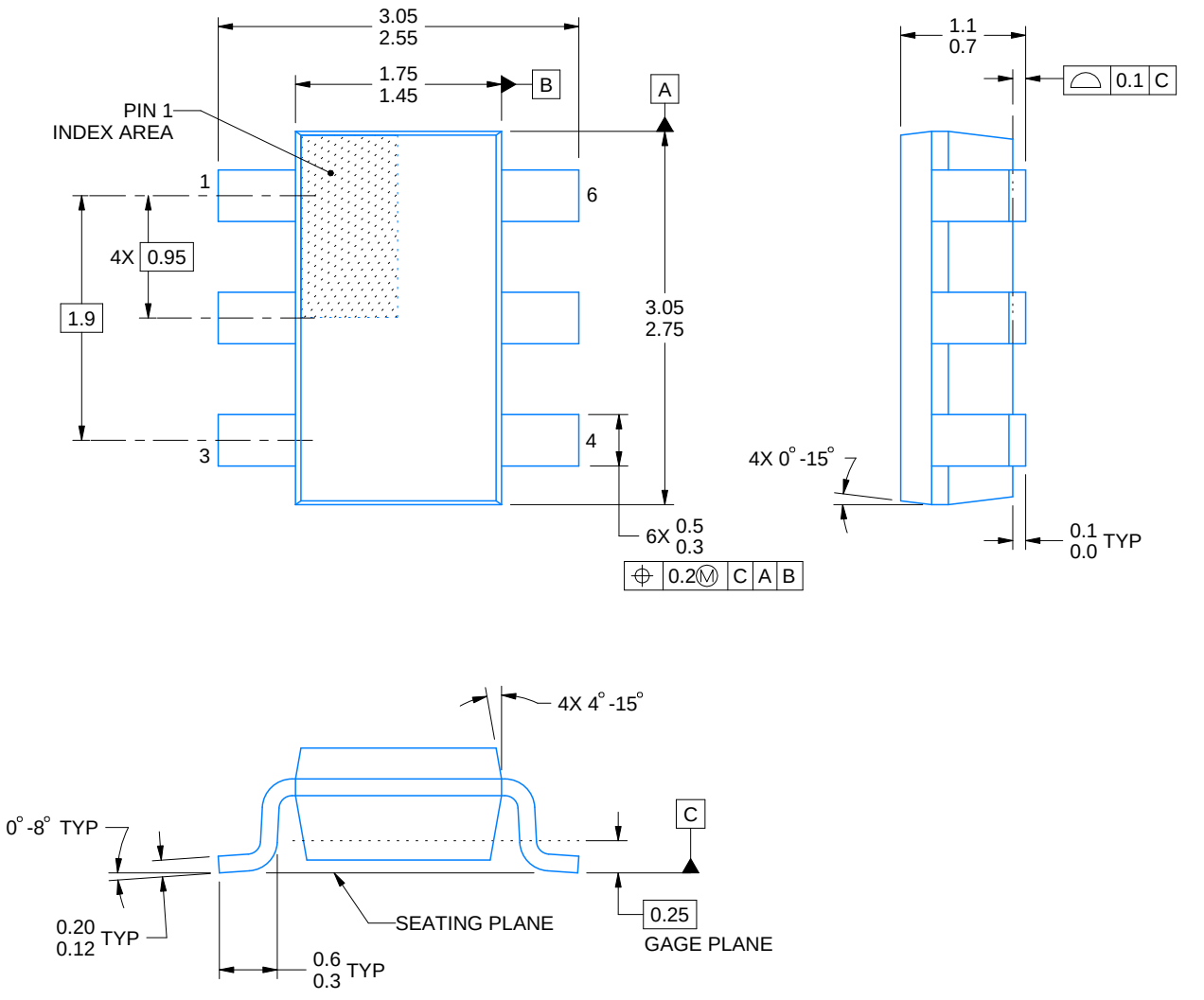
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV6710DDCR	SOT-23-THIN	DDC	6	3000	213.0	191.0	35.0
TLV6710DDCRG4	SOT-23-THIN	DDC	6	3000	213.0	191.0	35.0
TLV6710DDCT	SOT-23-THIN	DDC	6	250	213.0	191.0	35.0

PACKAGE OUTLINE

DDC0006A

SOT-23 - 1.1 max height

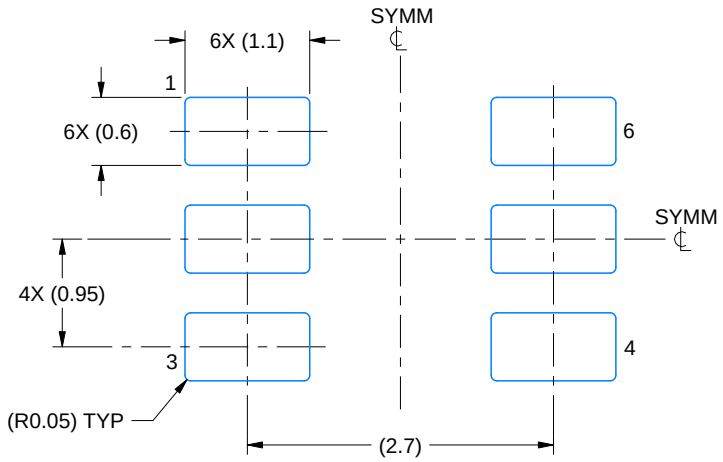
SMALL OUTLINE TRANSISTOR



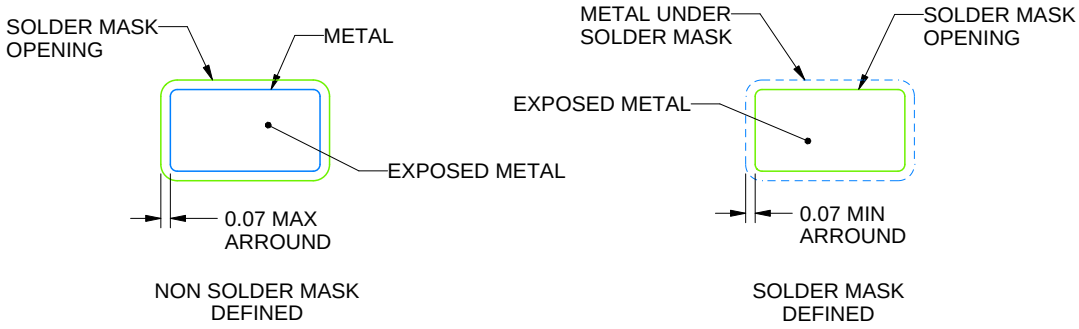
4214841/E 08/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-193.



LAND PATTERN EXAMPLE
EXPLOSED METAL SHOWN
SCALE:15X

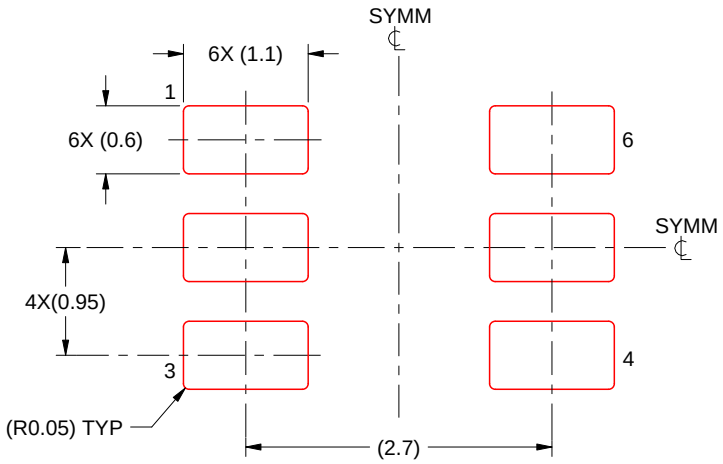


SOLDERMASK DETAILS

4214841/E 08/2024

NOTES: (continued)

4. Publication IPC-7351 may have alternate designs.
5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:15X

4214841/E 08/2024

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
7. Board assembly site may have different recommendations for stencil design.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES “AS IS” AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI’s products are provided subject to TI’s Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI’s provision of these resources does not expand or otherwise alter TI’s applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265